



### 30V N-Channel Enhancement Mode MOSFET

Voltage 30 V Current 3.9A

#### **Features**

- RDS(ON), VGS@10V, ID@3.9A<48mΩ</li>
- RDS(ON) , VGS@4.5V, ID@3.2A<53mΩ</li>
- RDS(ON), VGS@2.5V, ID@2.5A<66mΩ</li>
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

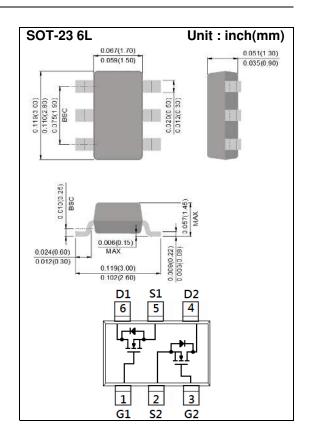
#### **Mechanical Data**

Case: SOT-23 6L Package

Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0005 ounces, 0.014 grams

Marking: ST0



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	30	V
Gate-Source Voltage		$V_{GS}$	<u>+</u> 12	V
Continuous Drain Current		ID	3.9	Α
Pulsed Drain Current		I <sub>DM</sub>	15.6	Α
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	1.25	W
	Derate above 25°C		10	mW/°C
Operating Junction and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55~150	°C
Typical Thermal Resistance - Junction to Ambient <sup>(Note 3)</sup>		R <sub>θ</sub> ЈА	100	°C/W





### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	-	-	V
Gate Threshold Voltage	$V_{\text{GS(th)}}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.4	0.72	1.2	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3.9A	-	41	48	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.2A	-	44	53	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =2.5A	-	51	66	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	0.01	1	uA
Gate-Source Leakage Current	Igss	V <sub>GS=+</sub> 12V, V <sub>DS</sub> =0V	-	<u>+</u> 10	<u>+</u> 100	nA
Dynamic						
Total Gate Charge	$Q_g$	$V_{DS}$ =15V, $I_{D}$ =3.9A, $V_{GS}$ =10V <sup>(Note 1,2)</sup>	-	11.3	-	nC
Gate-Source Charge	$Q_{gs}$		-	1.2	-	
Gate-Drain Charge	$Q_{gd}$		-	1.6	-	
Input Capacitance	Ciss	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V,	-	490	-	pF
Output Capacitance	Coss		-	44	-	
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	32	-	
Switching						
Turn-On Delay Time	td <sub>(on)</sub>	V <sub>DD</sub> =15V, I <sub>D</sub> =3.9A, V <sub>GS</sub> =10V,	-	2	-	ns
Turn-On Rise Time	tr		-	57	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	78	-	
Turn-Off Fall Time	tf	$R_G=6\Omega^{(Note\ 1,2)}$	-	79	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	Is		_	-	1.5	А
Diode Forward Current	.5					
Diode Forward Voltage	$V_{ extsf{SD}}$	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V	-	0.77	1.2	V

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
- 4. The maximum current rating is package limited





#### **TYPICAL CHARACTERISTIC CURVES**

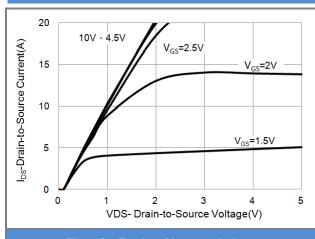


Fig.1 On-Region Characteristics

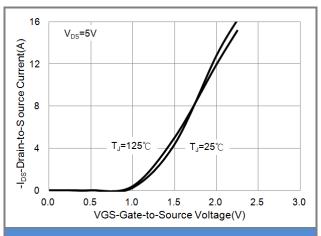


Fig.2 Transfer Characteristics

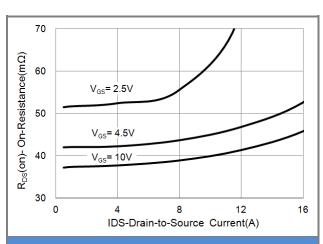


Fig.3 On-Resistance vs. Drain Current

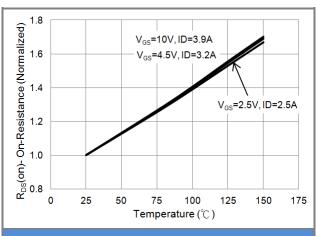


Fig.4 On-Resistance vs. Junction temperature

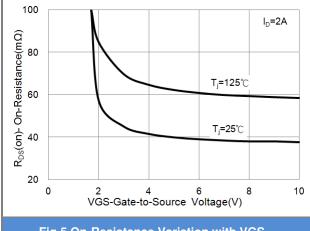
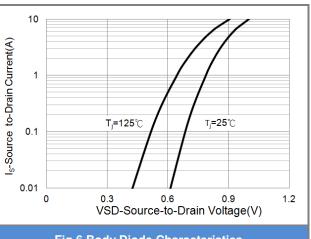


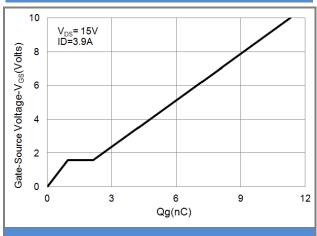
Fig.5 On-Resistance Variation with VGS.







#### **TYPICAL CHARACTERISTIC CURVES**



**Fig.7 Gate-Charge Characteristics** 

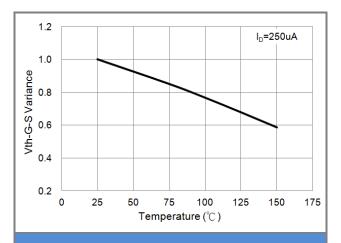


Fig.8 Threshold Voltage Variation with Temperature

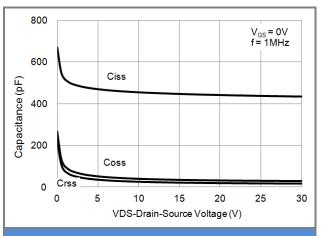


Fig.9 Capacitance vs. Drain-Source Voltage.

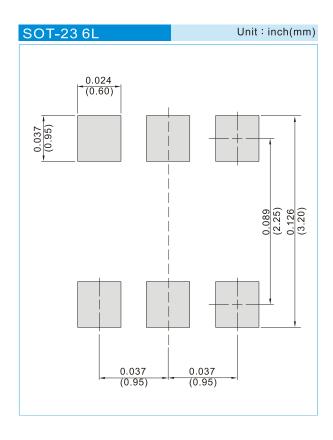




### PART NO. PACKING CODE VERSION

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJS6800_S1_00001	SOT-23 6L	3K pcs / 7" reel	ST0	Halogen free RoHS compliant
PJS6800_S2_00001	SOT-23 6L	10K pcs / 13" reel	ST0	Halogen free RoHS compliant

### **MOUNTING PAD LAYOUT**







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